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PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM 10011802	FILING DATE 12/12/2001	CLASS 324	SUBCLASS	GAU 2858	EXAMINER
**APPLICANTS: Yan Li-Nan, Wang Zhigang, Yan Li-Ten-Chun					
CONTINUING DATA VERIFIED:					
**FOREIGN APPLICATIONS VERIFIED:					
PG-PUB. DO NOT PUBLISH <input type="checkbox"/>		RESCIND <input type="checkbox"/>			
Foreign priority claimed <input type="checkbox"/> Yes <input type="checkbox"/> No		ATTORNEY DOCKETS NO			
US USC 119 conditions met <input type="checkbox"/> Yes <input type="checkbox"/> No		AMD-G0480			
Continuation Acknowledged Examiners initials					
TITLE: Method of determining gate oxide thickness of an operational MOSFET					

NOTICE OF ALLOWANCE MAILED		Assistant Examiner	CLAIMS ALLOWED	
			Total Claims	Print Claim for O.G.
ISSUE FEE		Primary Examiner	DRAWING	
Amount Due	Date Paid		Sheets Drawg.	Figs. Drawg.
<input type="checkbox"/> TERMINAL DISCLAIMER		PREPARED FOR ISSUE	Application Examiner	
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